

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claims 1-12 (canceled)

Claims 13-18 (withdrawn)

Claim 19 (canceled)

20 (new). An organic field effect transistor (OFET), comprising:
a gate dielectric layer on a substrate, said gate dielectric layer comprising at least one silsesquioxane precursor oligomer having phenyl pendant groups.

21 (new). The OFET recited in Claim 20, further comprising:
a gate electrode on said substrate, wherein said gate dielectric is on said gate electrode;
an organic semiconducting layer on said gate dielectric layer; and
a source electrode and a drain electrode in contact with said organic semiconducting layer.

22 (new). The OFET recited in Claim 20, further including another silsesquioxane precursor oligomer having methyl pendant groups.

23 (new). The OFET recited in Claim 20, further including another silsesquioxane precursor oligomer having dimethyl pendant groups.

24 (new). The OFET recited in Claim 20, wherein said silsesquioxane precursor oligomer is an alkyl(methyl)phenyl oligomer.

25 (new). The OFET recited in Claim 20, wherein said substrate comprises polyethylene terphthalate.

26 (new). The OFET recited in Claim 25, wherein said substrate is coated with indium tin oxide.

27 (new). The OFET recited in Claim 20, wherein said gate dielectric layer is a silane-reagent treated layer.

28 (new). The OFET recited in Claim 27, wherein said silane reagent is selected from the group $X-Si(OR^1)_m(R^2)_n$, where the values for m and n are from 0 to 3 and $m+n=3$; R^1 is an alkyl group having from 1 to 6 carbon atoms; R^2 is an alkyl group having from 1 to 16 carbon atoms or a halogen group; and X is a substituent selected from a substituted or unsubstituted aryl, $F_3C(F_2C)_9CH_2-$, the group $NH(Si)(CH_3)_3$; and a saturated or unsaturated alkyl or alkoxycarbonyl having from 6 to 20 carbon atoms.

29 (new). The OFET recited in Claim 28, wherein said silane reagent is selected from $F_3C(F_2C)_9CH_2-Si(OCH_3)_3$; $C_8H_{17}Si(OCH_3)(CH_3)_2$; $C_6H_5Si(OCH_3)_3$; $C_{18}H_{37}Si(OCH_3)_3$; $CH_2CH-C(O)-O-(CH_2)_3Si(OCH_3)(CH_3)_2$; $F_3C(F_2C)_9-Si(Cl)_3$; $Cl-CH_2SiCl_2CH_3$; and $(CH_3)_3SiNHSi(CH_3)_3$.